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APPLICATION NO.	I	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/616,508		07/10/2003	Hyeon Sang Shin	P69006US0	1777
136	7590	12/01/2004		EXAM	INER
		MAN PLLC	MITCHELL, JAMES M		
	400 SEVENTH STREET N.W. SUITE 600				PAPER NUMBER
WASHING	TON, DO	20004	2813		
				DATE MAILED: 12/01/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
·	10/616,508	SHIN, HYEON SANG
Office Action Summary	Examiner	Art Unit
	James M. Mitchell	2813
The MAILING DATE of this communication Period for Reply	appears on the cover sheet w	th the correspondence address
A SHORTENED STATUTORY PERIOD FOR RE THE MAILING DATE OF THIS COMMUNICATIO  - Extensions of time may be available under the provisions of 37 CFI after SIX (6) MONTHS from the mailing date of this communication  - If the period for reply specified above, the maximum statutory pe  - Failure to reply within the set or extended period for reply will, by st Any reply received by the Office later than three months after the m earned patent term adjustment. See 37 CFR 1.704(b).	N. R 1.136(a). In no event, however, may a r . reply within the statutory minimum of thir riod will apply and will expire SIX (6) MON atute, cause the application to become AE	eply be timely filed by (30) days will be considered timely. THS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).
Status		
<ul> <li>1) Responsive to communication(s) filed on 1</li> <li>2a) This action is FINAL.</li> <li>2b) 2b</li> <li>3) Since this application is in condition for alloclosed in accordance with the practice und</li> </ul>	This action is non-final. wance except for formal matt	-
Disposition of Claims		
4) ☐ Claim(s) 1-3 is/are pending in the application 4a) Of the above claim(s) is/are withen 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-3 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and	drawn from consideration.	
Application Papers		
9) The specification is objected to by the Exam  10) The drawing(s) filed on is/are: a) Applicant may not request that any objection to  Replacement drawing sheet(s) including the cor  11) The oath or declaration is objected to by the	accepted or b) objected to the drawing(s) be held in abeyar rection is required if the drawing	nce. See 37 CFR 1.85(a). (s) is objected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
12) △ Acknowledgment is made of a claim for fore a) △ All b) ☐ Some * c) ☐ None of:  1. △ Certified copies of the priority docum 2. ☐ Certified copies of the priority docum 3. ☐ Copies of the certified copies of the papplication from the International But * See the attached detailed Office action for a	ents have been received. ents have been received in A priority documents have been reau (PCT Rule 17.2(a)).	pplication No received in this National Stage
Attachment(s)		
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB, Paper No(s)/Mail Date	Paper No(s	iummary (PTO-413) s)/Mail Date nformal Patent Application (PTO-152) 

### **DETAILED ACTION**

This office action is in response to the application filed July 10, 2003.

## Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 1-3 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Claim 1 recites that a gate is divided around the oxide film, while drawings from your original disclosure appear to show in Figure 6 simply the formation of two gates. It is unclear how a gate is divided, without forming two individual gates.

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1 and 2 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nakamura al. (U.S. 6222,225) in combination with Ding (U.S. 6,743,675).

Nakamura discloses (Fig 5A-G) comprising the steps of: a method of forming a floating gate in a flash memory device, (a) forming a gate oxide film (15) on a semiconductor substrate (11); (b) depositing a first polysilicon film (16a) on the gate

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oxide film; (c) etching portions of the first polysilicon film, the gate oxide film and the semiconductor substrate to form a trench (Fig. 5B); (d) depositing an oxide film (14) for an isolation film on the entire top and then implementing a polishing process (Col. 6, Lines 33-43); (e) implementing an etch process using a dry etch method to etch the oxide film for the isolation film, thus forming the oxide film for the isolation film the top of which has a protrusion of a vertical nipple shape (Col. 6, Lines 48-57); and (f) depositing a second polysilicon film (5H; 16b) on a top surface to form a floating gate that is divided around the oxide film (14); (cl. 2) wherein the polishing step of (d) is CMP (Col.5, Line 36-39).

Nakamura does not appear to show forming a film over an entire surface and then implanting a polishing process to form a floating gate.

Ding utilizes a step of forming a film over an entire surface and then implanting a polishing process to form a floating gate (Col. 1, Lines 35-55; Col. 3, Lines 30-40).

It would have been obvious to one of ordinary skill in the art to form the second film of Nakamura over an entire surface of the chip and then implant a polishing process to form a floating gate as required by Nakamura (5G; 16).

### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to James M. Mitchell whose telephone number is (571) 272-1931. The examiner can normally be reached on M-F 8:00-4:00.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Novembér 18, 20